Indium-Tin Oxide (ITO) Thin Films Prepared by Sol-gel Spin-coating Process

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ITO thin film has been applied as a conductive transparent film for the optoelectronic devices, since it has high conductivity and transmittance in the range of visible light. In present, ITO films are fabricated mainly by a physical method such as a sputtering process. Wet chemical technique has been attempted as the simple and economic method for large-scale production as compared with other processes. In this study, Indium-Tin Oxide(ITO) films were prepared by a sol-gel process using Indium (III) acetylacetonate, Tin (IV) isopropoxide and 2-methoxyethanol. The mixed solutions were coated on soda-lime silicate glass substrate using a spin-coating process. The thickness of thin films was changed by repeating the coating and drying process. Then ITO thin films with the composition ratio of Sn/In in 8 wt% were crystallized under several thermal annealing conditions in the temperature range of 400° C to 800° C and 30-60 min in N_2 or Ar gas ITO crystal phase of film was detected by X-ray diffraction pattern. The effects of the firing and annealing conditions on electrical properties of ITO films were investigated. The ITO coatings exhibit the sheet resistance in range of $\sim 10^4 \, \Omega$ / and the transmission rate over 90% in visible light region.

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PMN-PZT 세라믹스의 소결거동 및 압전특성에 대한 Li₂O의 첨가효과

Effects of Li₂O Additive on the Sintering Behavior and Piezoelectric Properties of PMN-PZT Ceramics

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본 연구에서는 0 2Pb(Mg_{1/3}N_{1/23})O₃-0 8Pb(Zr_{0 475}Tı_{0 525})O₃계(이하 PMN-PZT) 세라믹스에 Lı₂O를 0 wt% ~0 3 wt% 첨가하여 소결거동 및 압전특성을 관찰하였다. PMN-PZT계 세라믹스에 Lı₂O를 첨가함에 따라 소성수축률 및 소성밀도가 향상되었으며, 소결온도를 1000℃ 이하로 낮출 수 있었다 Lı₂O를 첨가하지 않은 PMN-PZT계 세라믹스의 경우 양호한 압전특성을 얻기 위해서는 1200℃ 이상의 높은 소결온도를 요구하였으나, Lı₂O를 0 05 wt% 이상 첨가한 경우 900℃의 낮은 소성온도에서도 치밀화가 충분히 진행되었다 그러나 0 2 wt% 이상 Lı₂O를 첨가하게 되면 오히려 입자성장이 억제되고 유전 및 압전특성의 저하를 초래하였다. 그 결과 0 1 wt%의 Lı₂O를 첨가하여 1000℃에서 소결한 PMN-PZT 세라믹스의 전기기계결합계수(k_p)와 압전상수(d₃₃)가 각각 65.4%와 573 pC/N로 가장 높았다. 본 발표에서는 Lı₂O가 PMN-PZT 세라믹스의 미세구조에 미치는 영향을 유전 및 압전 특성과 연관하여 고찰할 것이다